

ABSTRACT OF THE DISCLOSURE

The intermediate layer material composition for a multilayer resist process in the present invention, which is soluble in an organic solvent, excellent in storage stability, and has no problem with regard to a footing shape, a pattern separation and a line edge roughness in patterning an upper resist, and a pattern formation process using the intermediate layer material composition, in which the intermediate layer material composition for a multilayer resist process, comprises a polymer (component A) containing a repeating unit having on a side chain thereof a specific structure containing a silicon atom-oxygen atom bond, and the pattern formation process using the same.